

ABSTRACT OF THE DISCLOSURE

A ferroelectric film wherein 5 to 40 mol% in total of at least one of Nb, V, and W is included in the B site of a $\text{Pb}(\text{Zr,Ti})\text{O}_3$ ferroelectric which includes at least
5 four-fold coordinated Si^{4+} or Ge^{4+} in the A site ion of a ferroelectric perovskite material in an amount of 1% or more. This enables to significantly improve reliability of the ferroelectric film.